

## KTC3207 TRANSISTOR (NPN)

### FEATURES

Power dissipation

$P_{CM}$ : 1 W ( $T_{amb}=25^{\circ}C$ )

Collector current

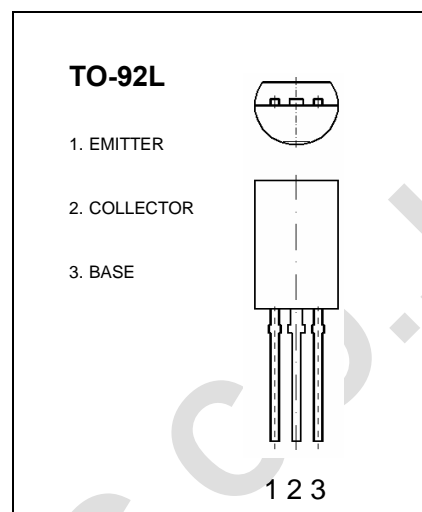
$I_{CM}$ : 100 mA

Collector-base voltage

$V_{(BR)CBO}$ : 300 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=240V, I_E=0$			1.0	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=7V, I_C=0$			1.0	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=4mA$	20			
	$h_{FE(2)}$	$V_{CE}=10V, I_C=20mA$	30		150	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=20mA$	50			MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=20V, I_E=0, f=1MHz$		3.0		pF